EE C245 – ME C218
Introduction to MEMS Design
Fall 2011

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Lecture Module 1: Admin & Overview

Instructor: Prof. Clark T.-C. Nguyen

- *Education*: Ph.D., University of California at Berkeley, 1994
- *1995*: joined the faculty of the Dept. of EECS at the University of Michigan
- *2006*: (came back) joined the faculty of the Dept. of EECS at UC Berkeley
- *Research*: exactly the topic of this course, with a heavy emphasis on vibrating RF MEMS
- *Teaching*: (at the UofM) mainly transistor circuit design courses; (UC Berkeley) 140, 143, 243, 245
- *2001*: founded Discera, the first company to commercialize vibrating RF MEMS technology
- *Mid-2002 to 2005*: DARPA MEMS program manager
  - ran 10 different MEMS-based programs
  - *topics*: power generation, chip-scale atomic clock, gas analyzers, nuclear power sources, navigation-grade gyros, on-chip cooling, micro environmental control

Course Overview

- Goals of the course:
  - Accessible to a broad audience (minimal prerequisites)
  - Design emphasis
    - Exposure to the techniques useful in analytical design of structures, transducers, and process flows
  - Perspective on MEMS research and commercialization circa 2011
- Related courses at UC Berkeley:
  - EE 143: Microfabrication Technology
  - EE 147: Introduction to MEMS
  - ME 119: Introduction to MEMS (mainly fabrication)
  - BioEng 121: Introduction to Micro and Nano Biotechnology and BioMEMS
  - ME C219 – EE C246: MEMS Design
- Assumed background for EE C245: graduate standing in engineering or physical/bio sciences

What Should You Know?

Typical mid-2000's CMOS Process (good down to ~0.25μm)

D G Sub S D G Sub S
S G D S G D
2nd level metal interconnect
1st level metal interconnect
CVD Tungsten
TiN local interconnect
LPCVD SiO_2
polysilicon gate
$TiSi_2$ contact barrier
LOCOS Oxidation
Lightly doped drain (LDD)
P+ N P+ N+ P N+
N Well - PMOS Substrate
P Well - NMOS Substrate
P

You should either already know or be able to learn independently & very quickly:

1. How to deposit or grow those different layers.
2. How to pattern or otherwise form the shapes of the layers shown.
3. What determines the order by which the different layers are formed, e.g., temperature limits, topography limits, etc...

We will review these things, but we will do this very fast!

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What Should You Know?

- Basic circuit analysis & design using op amps
- *Example*: Find the transfer function $v_o(s)/v_i(s)$ of the circuit below.

Ideal Op Amp: (apply when have neg. FB)
1. $v_- = v_+$
2. $R_i \to \infty$
3. $A_o = gain \to \infty$
4. $R_o = 0$

$v_o = -i_i\left(R_f \| \frac{1}{sC_f}\right) = -\frac{v_i}{R_1}\left(\frac{R_f}{1+sR_fC_f}\right)$

$\left[i_i = \frac{v_i}{R_1}\right]$

$\frac{v_o}{v_i}(s) = -\frac{R_f}{R_1}\frac{1}{1+sR_fC_f} = -\frac{R_f}{R_1}\frac{1}{1+\frac{s}{\omega_o}} \leftarrow \omega_o = \frac{1}{R_fC_f}$

Course Overview

- The mechanics of the course are summarized in the course handouts, given out in lecture today
  - Course Information Sheet
    - Course description
    - Course mechanics
    - Textbooks
    - Grading policy
  - Syllabus
    - Lecture by lecture timeline w/ associated reading sections
    - Midterm Exam: tentatively set for Thursday, Oct. 28
    - Final Exam: Friday, Dec. 17, 7-10 p.m.
    - Change this Final Exam time?
    - Project due date TBD (but near semester's end)

Lecture Outline

- Reading: Senturia, Chapter 1
- Lecture Topics:
  - Definitions for MEMS
  - MEMS roadmap
  - Benefits of Miniaturization

MEMS: Micro Electro Mechanical System

- A device constructed using micromachining (MEMS) tech.
- A micro-scale or smaller device/system that operates mainly via a mechanical or electromechanical means
- At least some of the signals flowing through a MEMS device are best described in terms of mechanical variables, e.g., displacement, velocity, acceleration, temperature, flow

Input: voltage, current acceleration, velocity light, heat …

MEMS

Output: voltage, current acceleration, velocity light, heat, …

Transducer to Convert Control to a Mechanical Variable (e.g., displacement, velocity, stress, heat, …)

Control: voltage, current acceleration velocity light, heat, …

[Wu, UCLA]

Angle set by mechanical means to control the path of light

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Other Common Attributes of MEMS

- Feature sizes measured in microns or less

80 mm
Gimballed, Spinning Macro-Gyroscope
MEMS Technology (for 80X size Reduction)
[Najafi, Michigan]
Micromechanical Vibrating Ring Gyroscope
1 mm
Signal Conditioning Circuits

- Merges computation with sensing and actuation to change the way we perceive and control the physical world
- Planar lithographic technology often used for fabrication
  - can use fab equipment identical to those needed for IC's
  - however, some fabrication steps transcend those of conventional IC processing

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Bulk Micromachining and Bonding

- Use the wafer itself as the structural material
- *Adv*: very large aspect ratios, thick structures
- *Example*: deep etching and wafer bonding

Micromechanical Vibrating Ring Gyroscope
1 mm
[Najafi, Michigan]
Silicon Substrate
Movable Structure
Electrode
Glass Substrate
Metal Interconnect
Anchor
[Pisano, UC Berkeley]
Microrotor (for a microengine)

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Surface Micromachining

Release Etch Barrier
Structural Material (e.g., polysilicon, nickel, etc.)
Sacrificial Oxide
Hydrofluoric Acid Release Solution
Silicon Substrate
pwell
Free-Standing Resonator Beam
Silicon Substrate
pwell

- Fabrication steps compatible with planar IC processing

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Single-Chip Ckt/MEMS Integration

- Completely monolithic, low phase noise, high-Q oscillator (effectively, an integrated crystal oscillator)

300 µm
Sustaining Amplifier
Comb-Transducer
Shuttle Mass
Folded-Beam Suspension
Anchors
Oscilloscope Output Waveform
[Nguyen, Howe 1993]

- To allow the use of >600°C processing temperatures, tungsten (instead of aluminum) is used for metallization

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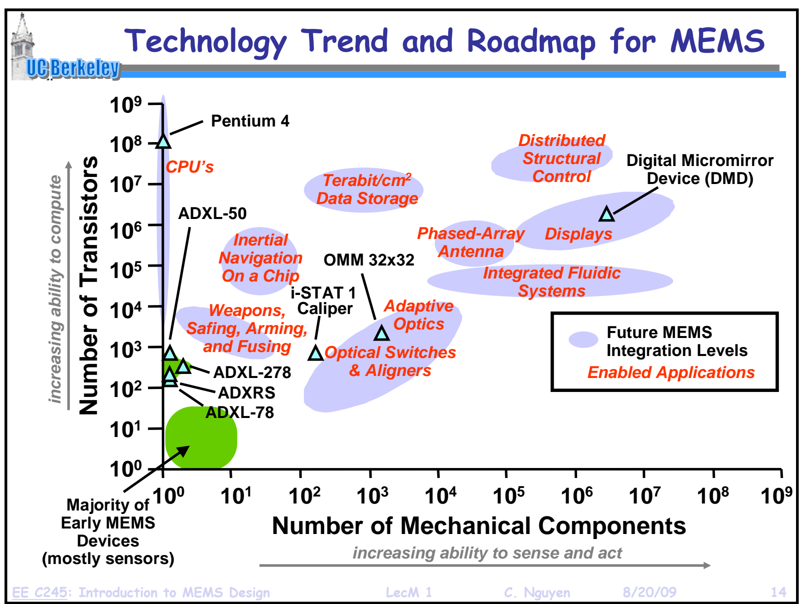
3D Direct-Assembled Tunable L

[Ming Wu, UCLA]



Example: Micromechanical Accelerometer

- *The MEMS Advantage:*
  - >30X size reduction for accelerometer mec...
  - allows integration w...

Tiny mass means small output ⇨ need integrated transistor circuits to compensate

Basic Operation Principle

x_o

$x \propto F_i = ma$

x

Displacement

Spring

a

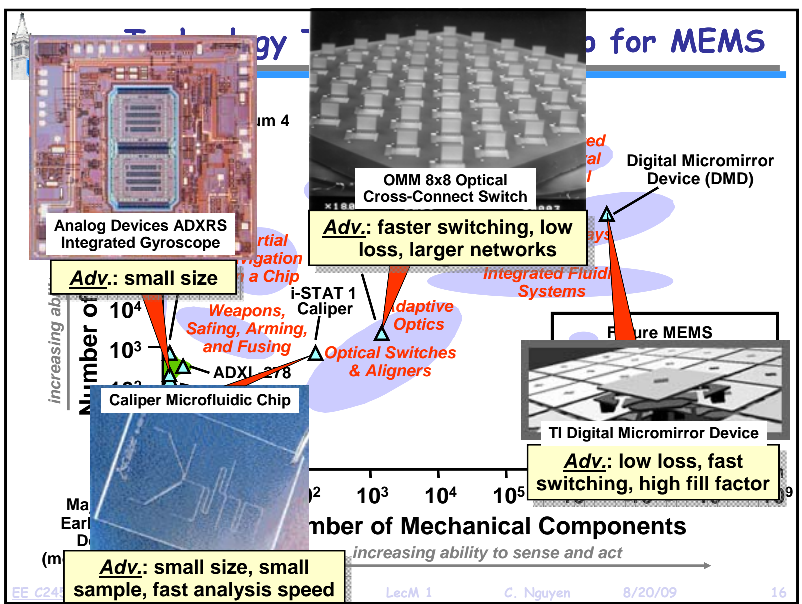
Inertial Force

Proof Mass

Acceleration

400 µm

Analog Devices ADXL 78



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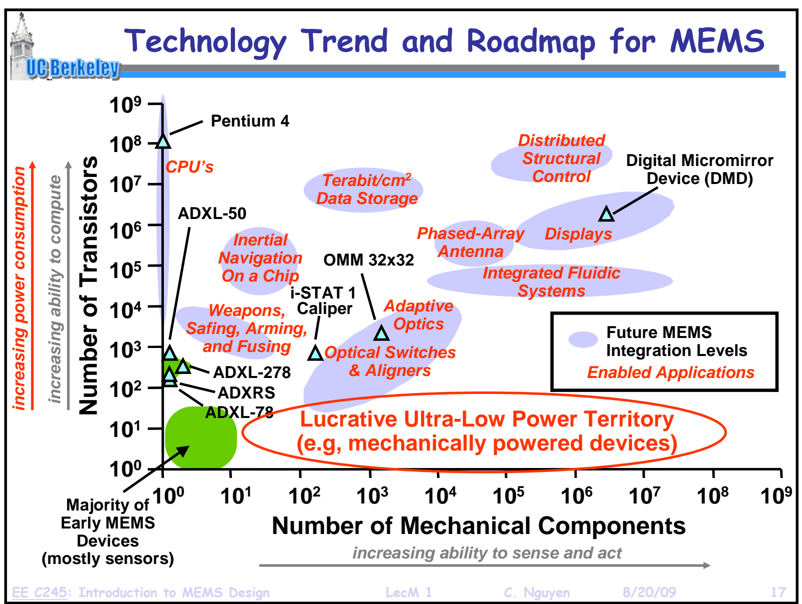
Technology Trend and Roadmap for MEMS



Benefits of Size Reduction: MEMS

- Benefits of size reduction clear for IC's in elect. domain
  - size reduction ⇨ speed, low power, complexity, economy
- MEMS: enables a similar concept, but …

MEMS extends the benefits of size reduction *beyond* the electrical domain

Performance enhancements for application domains beyond those satisfied by electronics in the same general categories

Speed	➡	Frequency ↑ , Thermal Time Const. ↓
Power Consumption	➡	Actuation Energy ↓ , Heating Power ↓
Complexity	➡	Integration Density ↑ , Functionality ↑
Economy	➡	Batch Fab. Pot. ↑ (esp. for packaging)
Robustness	➡	g-Force Resilience ↑

Vibrating RF MEMS

Basic Concept: Scaling Guitar Strings

Guitar String

Vib. Amplitude
Low Q
High Q
110 Hz
Freq.
Guitar
Vibrating "A" String (110 Hz)

Freq. Equation:

$$f_o = \frac{1}{2\pi}\sqrt{\frac{k_r}{m_r}}$$

Stiffness
Freq.
Mass

μMechanical Resonator

Metallized Electrode
W_r
L_r
Anchor
Polysilicon Clamped-Clamped Beam
h_r

[Bannon 1996]

f_o=8.5MHz
Q_{vac} =8,000
Q_{air} ~50

Transmission [dB]
Frequency [MHz]

Performance:
L_r=40.8μm
m_r ~ 10^{-13} kg
W_r=8μm, h_r=2μm
d=1000Å, V_P=5V
Press.=70mTorr

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